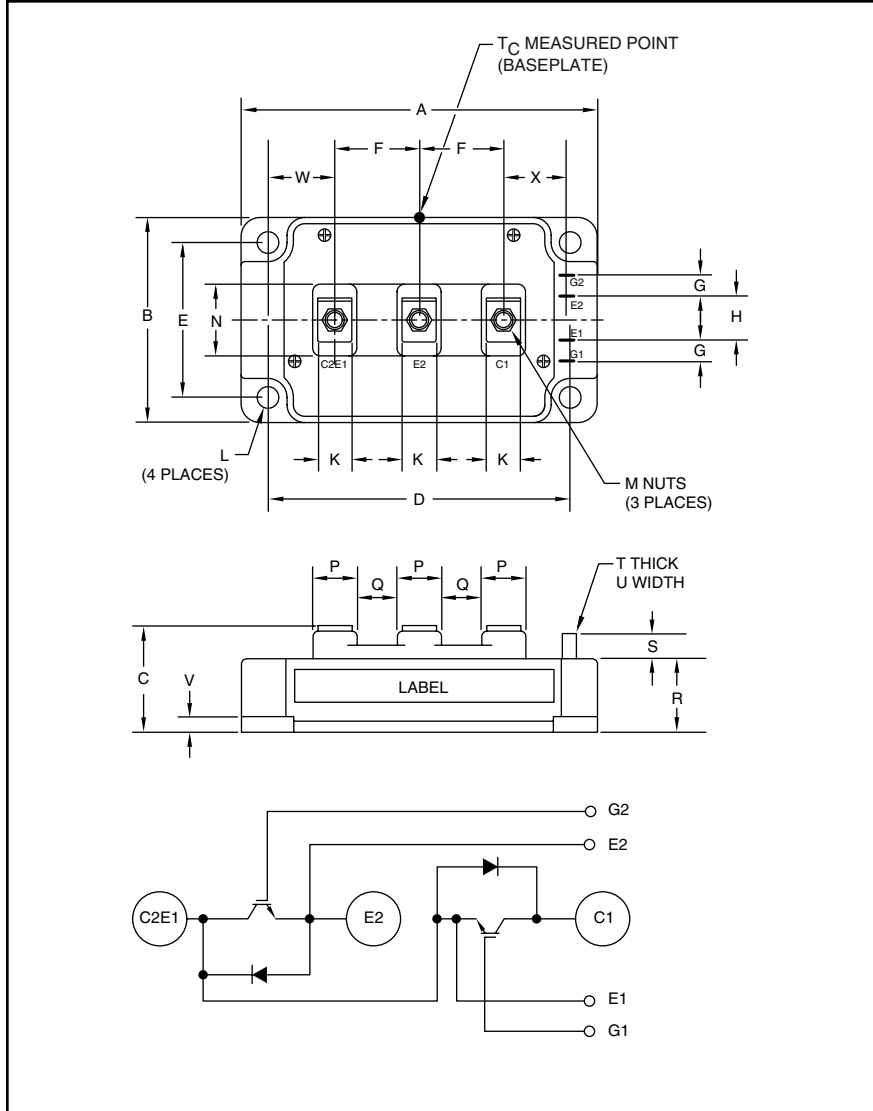


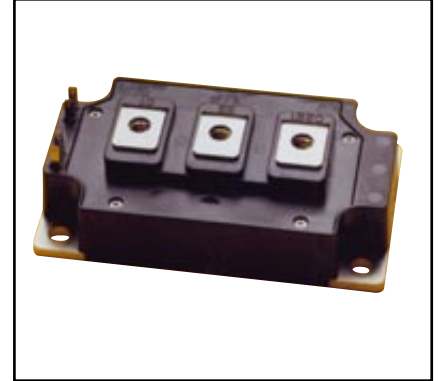
### Dual IGBTMOD™ NF-Series Module 200 Amperes/1200 Volts



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	4.25	108.0
B	2.44	62.0
C	1.18±0.4/-0.02	30.0±1.0/-0.5
D	3.66±0.01	93.0±0.25
E	1.89±0.01	48.0±0.25
F	0.98	25.0
G	0.24	6.0
H	0.59	15.0
K	0.55	14.0
L	0.26 Dia.	Dia. 6.5
M	M6 Metric	M6

Dimensions	Inches	Millimeters
N	1.18	30.0
P	0.71	18.0
Q	0.28	7.0
R	0.87	22.2
S	0.33	8.5
T	0.02	0.5
U	0.110	2.8
V	0.16	4.0
W	0.85	21.5
X	0.94	24.0



#### Description:

Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of two IGBT Transistors in a half-bridge configuration with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

#### Features:

- Low Drive Power
- Low  $V_{CE(sat)}$
- Discrete Super-Fast Recovery Free-Wheel Diode
- Isolated Baseplate for Easy Heat Sinking

#### Applications:

- AC Motor Control
- UPS
- Battery Powered Supplies

#### Ordering Information:

Example: Select the complete part module number you desire from the table below -i.e. CM200DY-24NF is a 1200V ( $V_{CES}$ ), 200 Ampere Dual IGBTMOD™ Power Module.

Type	Current Rating Amperes	$V_{CES}$ Volts (x 50)
CM	200	24

**CM200DY-24NF**  
**Dual IGBTMOD™ NF-Series Module**  
 200 Amperes/1200 Volts

**Absolute Maximum Ratings,  $T_j = 25\text{ °C}$  unless otherwise specified**

Ratings	Symbol	CM200DY-24NF	Units
Junction Temperature	$T_j$	-40 to 150	°C
Storage Temperature	$T_{stg}$	-40 to 125	°C
Collector-Emitter Voltage (G-E Short)	$V_{CES}$	1200	Volts
Gate-Emitter Voltage (C-E Short)	$V_{GES}$	±20	Volts
Collector Current*** (DC, $T_C = 112\text{ °C}$ )	$I_C$	200	Amperes
Peak Collector Current	$I_{CM}$	400*	Amperes
Emitter Current** ( $T_C = 25\text{ °C}$ )	$I_E$	200	Amperes
Peak Emitter Current**	$I_{EM}$	400*	Amperes
Maximum Collector Dissipation ( $T_C = 25\text{ °C}$ , $T_j \leq 150\text{ °C}$ )	$P_C$	1130	Watts
Mounting Torque, M6 Main Terminal	—	40	in-lb
Mounting Torque, M6 Mounting	—	40	in-lb
Weight	—	400	Grams
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	$V_{ISO}$	2500	Volts

**Static Electrical Characteristics,  $T_j = 25\text{ °C}$  unless otherwise specified**

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$	—	—	1.0	mA
Gate Leakage Current	$I_{GES}$	$V_{GE} = V_{GES}$ , $V_{CE} = 0V$	—	—	0.5	μA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$I_C = 20mA$ , $V_{CE} = 10V$	6.0	7.0	8.0	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 200A$ , $V_{GE} = 15V$ , $T_j = 25\text{ °C}$	—	1.8	2.5	Volts
		$I_C = 200A$ , $V_{GE} = 15V$ , $T_j = 125\text{ °C}$	—	2.0	—	Volts
Total Gate Charge	$Q_G$	$V_{CC} = 600V$ , $I_C = 200A$ , $V_{GE} = 15V$	—	1350	—	nC
Emitter-Collector Voltage**	$V_{EC}$	$I_E = 200A$ , $V_{GE} = 0V$	—	—	3.2	Volts

**Dynamic Electrical Characteristics,  $T_j = 25\text{ °C}$  unless otherwise specified**

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance	$C_{ies}$		—	—	47	nf
Output Capacitance	$C_{oes}$	$V_{CE} = 10V$ , $V_{GE} = 0V$	—	—	4	nf
Reverse Transfer Capacitance	$C_{res}$		—	—	0.9	nf
Inductive Load	Turn-on Delay Time	$V_{CC} = 600V$ , $I_C = 200A$ , $V_{GE1} = V_{GE2} = 15V$ , $R_G = 1.6\Omega$ ,	—	—	500	ns
	Rise Time					
Switch Time	Turn-off Delay Time	Inductive Load	—	—	600	ns
	Fall Time					
Diode Reverse Recovery Time**	$t_{rr}$	Switching Operation,	—	—	250	ns
Diode Reverse Recovery Charge**	$Q_{rr}$	$I_E = 200A$	—	7.5	—	μC

\*Pulse width and repetition rate should be such that device junction temperature ( $T_j$ ) does not exceed  $T_{j(max)}$  rating.

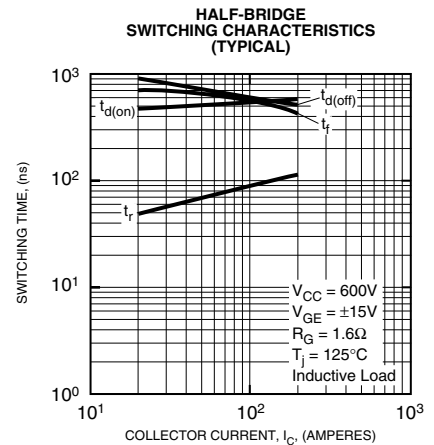
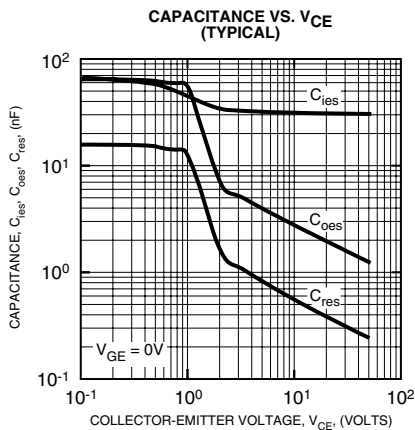
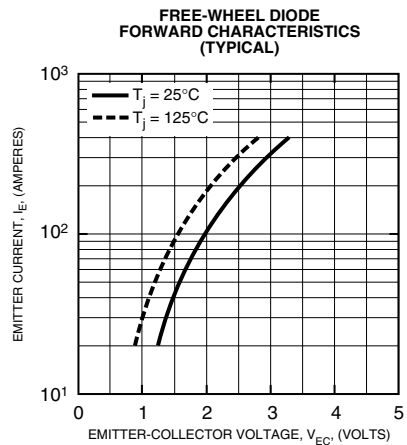
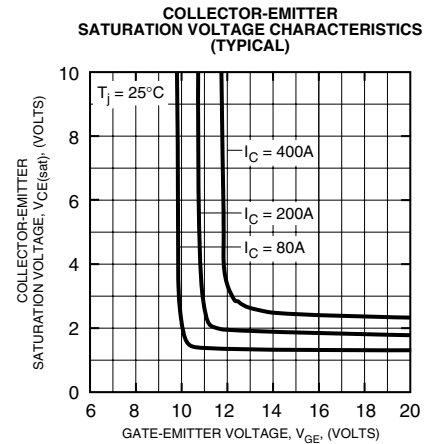
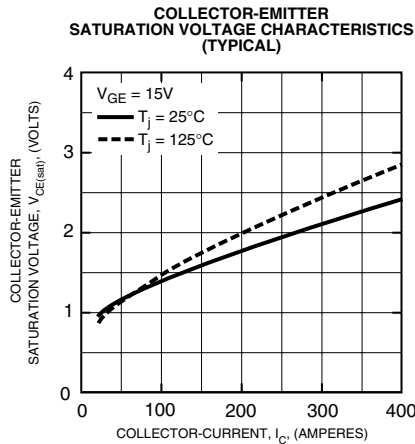
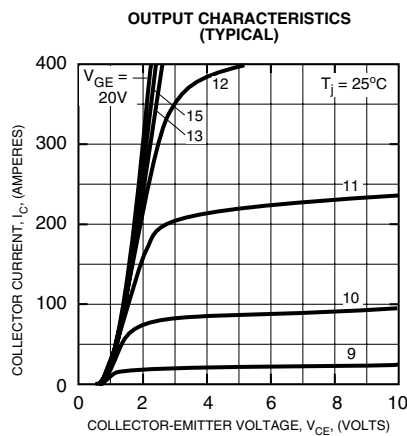
\*\*Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

\*\*\* $T_C$ : measured point is just under the chips. If this value is used,  $R_{th(f-a)}$  should be measured just under the chips.

**CM200DY-24NF**  
**Dual IGBTMOD™ NF-Series Module**  
 200 Amperes/1200 Volts

**Thermal and Mechanical Characteristics,  $T_j = 25^\circ\text{C}$  unless otherwise specified**

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)Q}$	Per IGBT 1/2 Module, $T_C$ Reference Point per Outline Drawing	—	—	0.11	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{th(j-c)D}$	Per FWDi 1/2 Module, $T_C$ Reference Point per Outline Drawing	—	—	0.19	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{th(j-c)'Q}$	Per IGBT 1/2 Module, $T_C$ Reference Point Under Chips	—	—	0.066	$^\circ\text{C/W}$
Contact Thermal Resistance	$R_{th(c-f)}$	Per 1/2 Module, Thermal Grease Applied	—	0.04	—	$^\circ\text{C/W}$
External Gate Resistance	$R_G$		1.6	—	16	$\Omega$



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